

**APPENDIX:
MARKED UP VERSION OF SPECIFICATION AND CLAIM AMENDMENTS**

Please amend claims 2-5 as follows:

2. The [switching device] method as defined in claim [1] 6 wherein the thickness of the backside p⁺ emitter is approximately between 0.2 and 1 μm.
3. The [switching device] method as defined in claim [1] 6 wherein the implanting dose of the backside p⁺ emitter is approximately between 1×10^{11} and 1×10^{17} cm⁻².
4. The [switching device] method as defined in claim [1] 6 wherein the thickness of the n-type residual diffused-layer contained in the n-type base is approximately between 5 and 50 μm.
5. The [switching device] method as defined in claim [1] 6 wherein the doping concentration of the n-type residual diffused-layer is in a range of approximately $1 \times 10^{14} \sim 1 \times 10^{17}$ cm⁻³ at the interface of the residual layer and the backside p⁺ emitter.